

■■ APPLICATION: High Voltage Switching Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	300	V
Collector-emitter voltage	V _{CEO}	300	V
Emitter-base voltage	V _{EBO}	7	V
Collector current	I _C	100	mA
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	30		150		V _{CE} = 10V, I _C = 20mA
Collector Cut-off Current	I _{CB0}			1	μA	V _{CB} = 240V, I _E =0
Emitter Cut-off Current	I _{EBO}			1	μA	V _{EB} = 7V, I _C =0
Collector-Base Breakdown Voltage	BV _{CB0}	300			V	I _C = 0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	300			V	I _C = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	7			V	I _E = 0.1mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			1	V	I _C = 10mA, I _B = 1mA
Base-Emitter Saturation Voltage	V _{BE(sat)}			1	V	I _C = 10mA, I _B = 1mA
Gain bandwidth product	f _T	50			MHz	I _C = 20mA, V _{CE} = 10V
Common Base Output Capacitance	C _{ob}		3		PF	V _{CB} = 20V, I _E =0, f = 1MHz

■■ h_{FE} Classification

Classification	
h _{FE}	30~150